

# **ISC Silicon NPN Power Transistors**

# **NJW3281G**

### **DESCRIPTION**

- · With TO-3PN packaging
- · Reliable performance at higher powers
- · Accurate reproduction of Input signal
- · Greater dynamic range
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

- Switching regulators
- · High frequency inverters
- General purpose power amplifiers

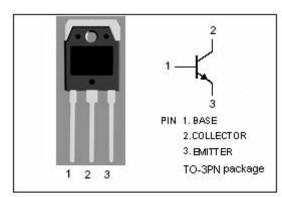


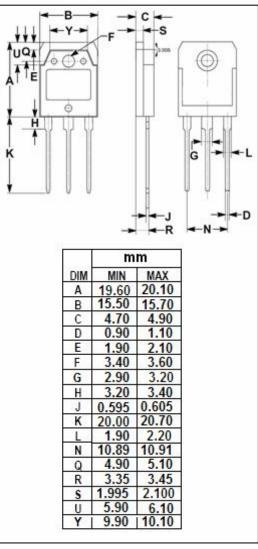
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	250	V
V <sub>CEO</sub>	Collector-Emitter Voltage	250	V
V <sub>CEX</sub>	Collector-Emitter Voltage V <sub>EB</sub> = 5V	250	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	15	Α
I <sub>CM</sub>	Collector Current-Peak	30	Α
lв	Base Current-Continuous	1.6	Α
P <sub>T</sub>	Total Power Dissipation @ T <sub>C</sub> =25℃	200	W
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case		°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100mA; I <sub>B</sub> = 0	250			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 0.8A			0.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 8A;V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 250V			50	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 250V			50	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V			5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	75		150	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	75		150	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	75		150	
h <sub>FE-4</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	60			
h <sub>FE-5</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	45			

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